

10/781,479

Ref #	Hits	Search Query	DBs	Default Operator	Plurals	Time Stamp
L1	0	(magnetic adj element) and MTJ and (magnetic adl tunnel adj junction) and ALN and SiN and (magnetic adj memory)	USPAT	OR	ON	2005/03/22 14:16
L2	2	(magnetic adj element) and MTJ and (magnetic adl tunnel adj junction) and SiN and (magnetic adj memory)	USPAT	OR	ON	2005/03/22 14:17
L3	1	(magnetic adj element) and MTJ and (magnetic adl tunnel adj junction) and SiN and (magnetic adj memory) and MRAM	USPAT	OR	ON	2005/03/22 14:16
L4	44	(magnetic adj element) and MTJ and (magnetic adl tunnel adj junction) and portion and plurality and sides and MRAM	USPAT	OR	ON	2005/03/22 14:18
L5	43	(magnetic adj element) and MTJ and (magnetic adj tunnel adj junction) and portion and plurality and sides and MRAM	USPAT	OR	ON	2005/03/22 14:18
L6	0	(magnetic adj element) and MTJ and (magnetic adj tunnel adj junction) and portion and plurality and sides and MRAM and (plurality adj2 sides) and passivation	USPAT	OR	ON	2005/03/22 14:19
L7	0	(magnetic adj element) and MTJ and (magnetic adj tunnel adj junction) and portion and plurality and sides and MRAM and (plurality adj2 sides)	USPAT	OR	ON	2005/03/22 14:19
L8	0	(magnetic adj element) and MTJ and (magnetic adj tunnel adj junction) and portion and plurality and sides and MRAM and passivation	USPAT	OR	ON	2005/03/22 14:19
L9	0	(magnetic adj element) and MTJ and (magnetic adj tunnel adj junction) and portion and plurality and sides and MRAM and protection and dielectric	USPAT	OR	ON	2005/03/22 14:20
L10	2	(magnetic adj element) and MTJ and (magnetic adj tunnel adj junction) and portion and plurality and sides and MRAM and SiN	USPAT	OR	ON	2005/03/22 14:20
L11	353	257/68	USPAT	OR	ON	2005/03/22 14:20
L12	128	257/108	USPAT	OR	ON	2005/03/22 14:20
L13	103	257/259	USPAT	OR	ON	2005/03/22 14:21

L14	2453	257/295	USPAT	OR	ON	2005/03/22 14:21
L15	3803	257/296	USPAT	OR	ON	2005/03/22 14:21
L16	650	257/421	USPAT	OR	ON	2005/03/22 14:21
L17	87	257/424	USPAT	OR	ON	2005/03/22 14:21
L18	282	257/422	USPAT	OR	ON	2005/03/22 14:21
L19	1	("6391483").PN.	USPAT	OR	OFF	2005/03/22 14:22
L20	1	("6744086").PN.	USPAT	OR	OFF	2005/03/22 14:22
L21	1	("6737283").PN.	USPAT	OR	OFF	2005/03/22 14:22
L22	1	19 and (AlN or SiN or SiNH or TaO or element or elements or memory or MRAM or side or sides or portion or plurality or magnetic or passivation or spacer or dielectric or insulator or insulating or pin or pinned or reside or free or stoichiometry or word or bit or line)	USPAT	OR	ON	2005/03/22 14:22
L23	1	20 and (AlN or SiN or SiNH or TaO or element or elements or memory or MRAM or side or sides or portion or plurality or magnetic or passivation or spacer or dielectric or insulator or insulating or pin or pinned or reside or free or stoichiometry or word or bit or line)	USPAT	OR	ON	2005/03/22 14:22
L24	1	21 and (AlN or SiN or SiNH or TaO or element or elements or memory or MRAM or side or sides or portion or plurality or magnetic or passivation or spacer or dielectric or insulator or insulating or pin or pinned or reside or free or stoichiometry or word or bit or line)	USPAT	OR	ON	2005/03/22 14:23
S39 4	102	(magnetic adj element) and MTJ and (magnetic adl tunnel adj junction)	USPAT	OR	ON	2005/03/22 11:29
S39 5	0	(magnetic adj element) and MTJ and (magnetic adl tunnel adj junction) and ALN and SiN and SiNH and TaO	USPAT	OR	ON	2005/03/22 14:15
S39 6	0	(magnetic adj element) and MTJ and (magnetic adl tunnel adj junction) and portion and plurality and sides and passivation	USPAT	OR	ON	2005/03/22 11:31

S39 7	47	(magnetic adj element) and MTJ and (magnetic adl tunnel adj junction) and portion and plurality and sides	USPAT	OR	ON	2005/03/22 14:17
S39 8	1144535	(magnetic adj element) and MTJ and (magnetic adl tunnel adj junction) and portion and plurality and sides and Si N	USPAT	OR	ON	2005/03/22 11:33
S39 9	3	(magnetic adj element) and MTJ and (magnetic adl tunnel adj junction) and portion and plurality and sides and SiN	USPAT	OR	ON	2005/03/22 11:35
S40 0	1	(magnetic adj element) and MTJ and (magnetic adl tunnel adj junction) and portion and plurality and sides and SiN and (magnetic adj memory) and MRAM	USPAT	OR	ON	2005/03/22 11:36
S40 1	3	S399 and (AlN or SiN or SiNH or TaO or element or elements or memory or MRAM or side or sides or portion or plurality or magnetic or passivation or spacer or dielectric or insulator or insulating or pin or pinned or reside or free or stoichiometry or word or bit or line)	USPAT	OR	ON	2005/03/22 14:22